

Welcome to **E-XFL.COM**

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded - Microcontrollers</u>"

Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I ² C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	4K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-VFBGA
Supplier Device Package	64-VFBGA (4x4)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f100leabg-u0

Table 1-1. List of Ordering Part Numbers

(2/12)

				(2/12)
Pin	Package	Data	Fields of	Ordering Part Number
count		flash	Application	
			Note	
25 pins	25-pin plastic	Mounted	Α	R5F1008AALA#U0, R5F1008CALA#U0, R5F1008DALA#U0,
25 pins	· · ·	Mounted	7.	R5F1008EALA#U0
	WFLGA (3 \times 3 mm,			R5F1008AALA#W0, R5F1008CALA#W0, R5F1008DALA#W0,
	0.5 mm pitch)			R5F1008EALA#W0
			G	R5F1008AGLA#U0, R5F1008CGLA#U0, R5F1008DGLA#U0,
				R5F1008EGLA#U0
				R5F1008AGLA#W0, R5F1008CGLA#W0, R5F1008DGLA#W0,
				R5F1008EGLA#W0
		Not	Α	R5F1018AALA#U0, R5F1018CALA#U0, R5F1018DALA#U0,
i		mounted		R5F1018EALA#U0
				R5F1018AALA#W0, R5F1018CALA#W0, R5F1018DALA#W0,
				R5F1018EALA#W0
30 pins	30-pin plastic LSSOP	Mounted	Α	R5F100AAASP#V0, R5F100ACASP#V0, R5F100ADASP#V0,
i	(7.62 mm (300), 0.65			R5F100AEASP#V0, R5F100AFASP#V0, R5F100AGASP#V0
	mm pitch)			R5F100AAASP#X0, R5F100ACASP#X0, R5F100ADASP#X0
	min piton)		_	R5F100AEASP#X0, R5F100AFASP#X0, R5F100AGASP#X0
			D	R5F100AADSP#V0, R5F100ACDSP#V0, R5F100ADDSP#V0,
				R5F100AEDSP#V0, R5F100AFDSP#V0, R5F100AGDSP#V0
				R5F100AADSP#X0, R5F100ACDSP#X0, R5F100ADDSP#X0, R5F100AEDSP#X0, R5F100AFDSP#X0, R5F100AGDSP#X0
			G	R5F100AGSP#V0, R5F100ACGSP#V0,
			G	R5F100ADGSP#V0, R5F100ACGSF#V0,
				R5F100AFGSP#V0, R5F100AGGSP#V0,
				R5F100AAGSP#X0, R5F100ACGSP#X0,
				R5F100ADGSP#X0,R5F100AEGSP#X0,
				R5F100AFGSP#X0, R5F100AGGSP#X0
		Not	Α	R5F101AAASP#V0, R5F101ACASP#V0, R5F101ADASP#V0,
				R5F101AEASP#V0, R5F101AFASP#V0, R5F101AGASP#V0
		mounted		R5F101AAASP#X0, R5F101ACASP#X0, R5F101ADASP#X0,
				R5F101AEASP#X0, R5F101AFASP#X0, R5F101AGASP#X0
			D	R5F101AADSP#V0, R5F101ACDSP#V0, R5F101ADDSP#V0,
				R5F101AEDSP#V0, R5F101AFDSP#V0, R5F101AGDSP#V0
				R5F101AADSP#X0, R5F101ACDSP#X0, R5F101ADDSP#X0,
				R5F101AEDSP#X0, R5F101AFDSP#X0, R5F101AGDSP#X0
32 pins	32-pin plastic	Mounted	Α	R5F100BAANA#U0, R5F100BCANA#U0, R5F100BDANA#U0,
	HWQFN (5 × 5 mm,			R5F100BEANA#U0, R5F100BFANA#U0, R5F100BGANA#U0
	0.5 mm pitch)			R5F100BAANA#W0, R5F100BCANA#W0, R5F100BDANA#W0,
	0.5 min pitch)			R5F100BEANA#W0, R5F100BFANA#W0, R5F100BGANA#W0
			D	R5F100BADNA#U0, R5F100BCDNA#U0, R5F100BDDNA#U0,
				R5F100BEDNA#U0, R5F100BFDNA#U0, R5F100BGDNA#U0
				R5F100BADNA#W0, R5F100BCDNA#W0, R5F100BDDNA#W0,
				R5F100BEDNA#W0, R5F100BFDNA#W0, R5F100BGDNA#W0
			G	R5F100BAGNA#U0, R5F100BCGNA#U0, R5F100BDGNA#U0,
				R5F100BEGNA#U0, R5F100BFGNA#U0, R5F100BGGNA#U0
				R5F100BAGNA#W0, R5F100BCGNA#W0, R5F100BDGNA#W0,
			_	R5F100BEGNA#W0, R5F100BFGNA#W0, R5F100BGGNA#W0
		Not	Α	R5F101BAANA#U0, R5F101BCANA#U0, R5F101BDANA#U0,
		mounted		R5F101BEANA#U0, R5F101BFANA#U0, R5F101BGANA#U0
				R5F101BAANA#W0, R5F101BCANA#W0, R5F101BDANA#W0,
			D	R5F101BEANA#W0, R5F101BFANA#W0, R5F101BGANA#W0
			٦ ا	R5F101BADNA#U0, R5F101BCDNA#U0, R5F101BDDNA#U0, R5F101BEDNA#U0, R5F101BEDNA#U0
1				R5F101BADNA#W0, R5F101BCDNA#W0, R5F101BDDNA#W0,
				R5F101BEDNA#W0, R5F101BCDNA#W0, R5F101BBDNA#W0,
			1	TOT TO TO EDINA#WO, NOT TO TO FOUNA#WO, NOT TO TO EDINA#WO

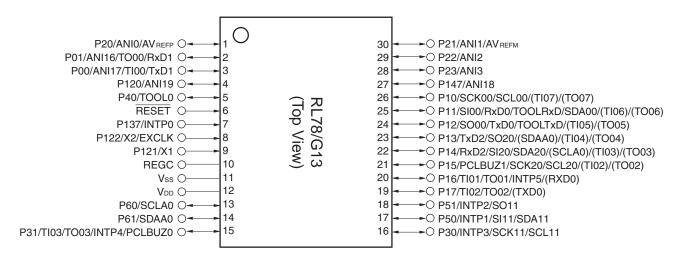
Note For the fields of application, refer to Figure 1-1 Part Number, Memory Size, and Package of RL78/G13.

Caution The ordering part numbers represent the numbers at the time of publication. For the latest ordering part numbers, refer to the target product page of the Renesas Electronics website.



1.3.4 30-pin products

• 30-pin plastic LSSOP (7.62 mm (300), 0.65 mm pitch)



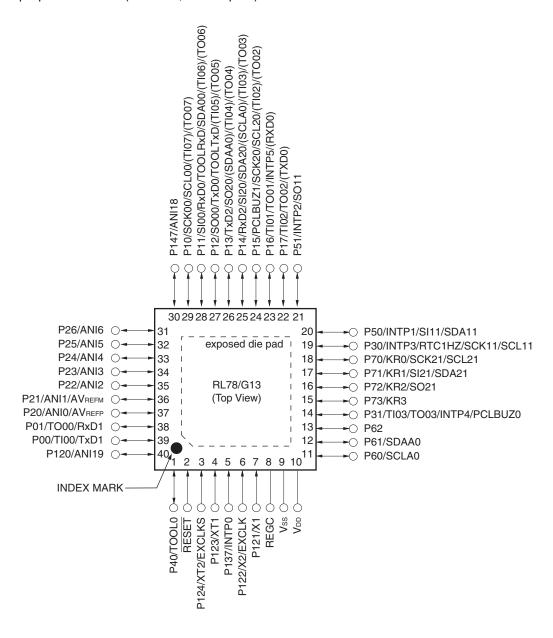
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

1.3.7 40-pin products

• 40-pin plastic HWQFN (6 × 6 mm, 0.5 mm pitch)



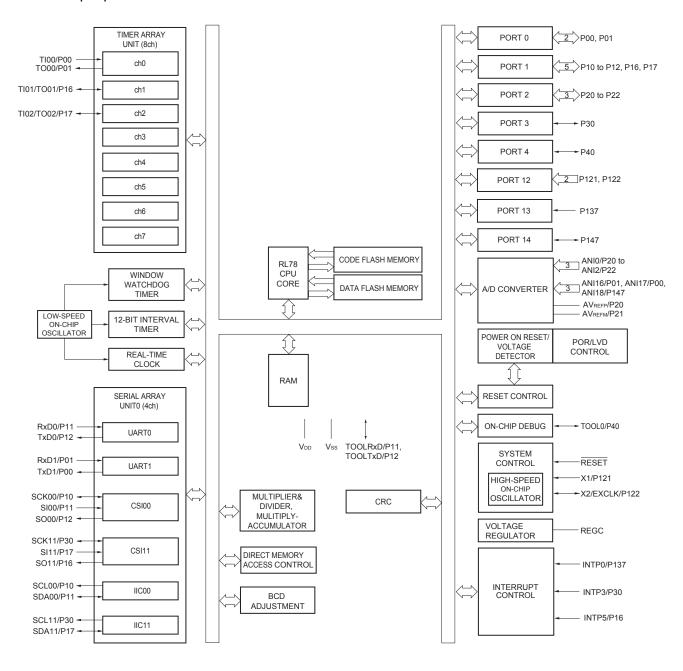
Caution Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F).

Remarks 1. For pin identification, see 1.4 Pin Identification.

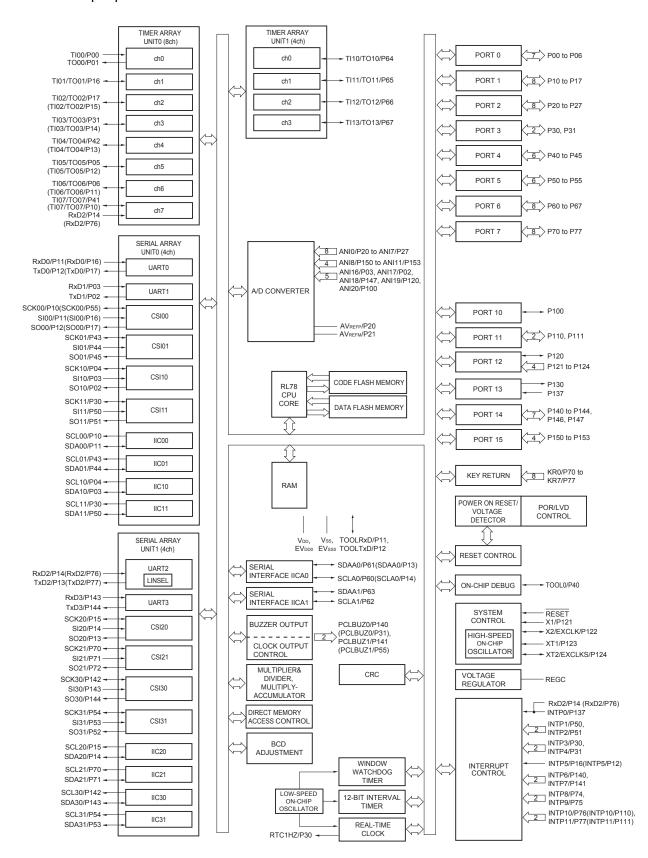
- Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.
- 3. It is recommended to connect an exposed die pad to Vss.

1.5 Block Diagram

1.5.1 20-pin products



1.5.12 80-pin products



Remark Functions in parentheses in the above figure can be assigned via settings in the peripheral I/O redirection register (PIOR). Refer to Figure 4-8 Format of Peripheral I/O Redirection Register (PIOR) in the RL78/G13 User's Manual.

2. The number of PWM outputs varies depending on the setting of channels in use (the number of masters and slaves) (see 6.9.3 Operation as multiple PWM output function in the RL78/G13 User's Manual).

3. When setting to PIOR = 1

(2/2)

										(2)	(2)
Ite	m	40-	pin	44	pin	48-	pin	52	-pin	64	-pin
		R5F100Ex	R5F101Ex	R5F100Fx	R5F101Fx	R5F100Gx	R5F101Gx	R5F100Jx	R5F101Jx	R5F100Lx	R5F101Lx
Clock output/buzz	er output	2	2		2		2		2		2
·	·	(Main s	system clo	ock: fmain = 1.024 kHz	Hz, 1.25 M 20 MHz o 2, 2.048 kH 2.768 kHz	peration) Iz, 4.096 k	:Hz, 8.192			2.768 kHz	
8/10-bit resolution	A/D converter	9 channels 10 channels 12 channels 12 channels						nels			
Serial interface	 [40-pin, 44-pin products] CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [48-pin, 52-pin products] CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 1 channel/simplified I²C: 1 channel/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel [64-pin products] CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART: 1 channel CSI: 2 channels/simplified I²C: 2 channels/UART (UART supporting LIN-bus): 1 channel 1 channel 1 channel 1 channel 										
accumulator DMA controller	uei/munpiy-	 16 bits × 16 bits = 32 bits (Unsigned or signed) 32 bits ÷ 32 bits = 32 bits (Unsigned) 16 bits × 16 bits + 32 bits = 32 bits (Unsigned or signed) 2 channels 									
Vectored	Internal		7	1	27		27		27		27
interrupt sources	External		7		7		10		12		 13
Key interrupt	1	4	1		4		6		8		8
Reset		Reset by RESET pin Internal reset by watchdog timer Internal reset by power-on-reset Internal reset by voltage detector Internal reset by illegal instruction execution Note Internal reset by RAM parity error Internal reset by illegal-memory access									
Power-on-reset ci	rcuit	Power- Power-		1.51 V et: 1.50 V	` ,						
Voltage detector		Rising Falling	-		to 4.06 V (to 3.98 V (
On-chip debug fur	nction	Provided									
Power supply volt	age	V _{DD} = 2.4	to 5.5 V ($T_A = -40 \text{ to}$ $T_A = -40 \text{ to}$	+105°C)						
Operating ambien	t temperature				ier applica rial applica		ndustrial a	pplications	s)		

Note The illegal instruction is generated when instruction code FFH is executed.

Reset by the illegal instruction execution not issued by emulation with the in-circuit emulator or on-chip debug emulator.

<R>

[80-pin, 100-pin, 128-pin products]

Caution This outline describes the functions at the time when Peripheral I/O redirection register (PIOR) is set to 00H.

(1/2)

	Itam	90	nin	100	nin	100	(1/Z)			
	Item	80- R5F100Mx	R5F101Mx	R5F100Px	-pin R5F101Px	128 R5F100Sx	R5F101Sx			
Code flash me	emory (KB)		512		o 512		o 512			
Data flash me	- , ,	8	=	8	=	8	=			
RAM (KB)		8 to 3	2 Note 1	8 to 3	2 Note 1	16 to 3	32 Note 1			
Address spac	е	1 MB		1						
Main system clock	High-speed system clock	HS (High-speed HS (High-speed LS (Low-speed	I main) mode: 1 I main) mode: 1 main) mode: 1	external main sys to 20 MHz (V _{DD} = to 16 MHz (V _{DD} = to 8 MHz (V _{DD} = to 4 MHz (V _{DD} =	= 2.7 to 5.5 V), = 2.4 to 5.5 V), 1.8 to 5.5 V),	(EXCLK)				
	High-speed on-chip oscillator	HS (High-speed LS (Low-speed	(High-speed main) mode: 1 to 32 MHz (V _{DD} = 2.7 to 5.5 V), (High-speed main) mode: 1 to 16 MHz (V _{DD} = 2.4 to 5.5 V), (Low-speed main) mode: 1 to 8 MHz (V _{DD} = 1.8 to 5.5 V), (Low-voltage main) mode: 1 to 4 MHz (V _{DD} = 1.6 to 5.5 V) 1 (crystal) oscillation, external subsystem clock input (EXCLKS)							
Subsystem cl	ock	XT1 (crystal) os 32.768 kHz	cillation, externa	l subsystem cloc	k input (EXCLKS	5)				
Low-speed or	n-chip oscillator	15 kHz (TYP.)								
General-purpo	ose register	(8-bit register \times 8) \times 4 banks								
Minimum insti	ruction execution time	0.03125 μs (Hig	h-speed on-chip	oscillator: fiн = 3	2 MHz operation)				
		0.05 μs (High-speed system clock: f _{MX} = 20 MHz operation)								
		30.5 <i>μ</i> s (Subsys	stem clock: fsub =	= 32.768 kHz ope	ration)					
Instruction se	t	 Data transfer (8/16 bits) Adder and subtractor/logical operation (8/16 bits) Multiplication (8 bits × 8 bits) Rotate, barrel shift, and bit manipulation (Set, reset, test, and Boolean operation), etc. 								
I/O port	Total	7	'4	9	92	1	20			
	CMOS I/O	(N-ch O.D. I/O	64 [EV _{DD} withstand e]: 21)	(N-ch O.D. I/O	32 [EV _{DD} withstand je]: 24)	(N-ch O.D. I/O	10 [EV _{DD} withstand e]: 25)			
	CMOS input	!	5		5		5			
	CMOS output		1		1		1			
	N-ch O.D. I/O (withstand voltage: 6 V)		4		4		4			
Timer	16-bit timer	12 cha	nnels	12 cha	annels	16 cha	annels			
	Watchdog timer	1 cha	ınnel	1 cha	annel	1 cha	annel			
	Real-time clock (RTC)	1 cha	nnel	1 cha	annel	1 cha	annel			
	12-bit interval timer (IT)	1 cha	nnel	1 cha	annel	1 cha	annel			
	Timer output	12 channels (PWM outputs: 10 Note 2) 12 channels (PWM outputs: 10 Note 2) 16 channels (PWM outputs: 14 Note 2)								
	RTC output	1 channel • 1 Hz (subsyst	em clock: fsub =	32.768 kHz)						

Notes 1. The flash library uses RAM in self-programming and rewriting of the data flash memory.

The target products and start address of the RAM areas used by the flash library are shown below.

R5F100xJ, R5F101xJ (x = M, P): Start address FAF00H R5F100xL, R5F101xL (x = M, P, S): Start address F7F00H

For the RAM areas used by the flash library, see Self RAM list of Flash Self-Programming Library for RL78 Family (R20UT2944).

2.2 Oscillator Characteristics

2.2.1 X1, XT1 oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Parameter	Resonator	Conditions	MIN.	TYP.	MAX.	Unit
X1 clock oscillation frequency (fx) ^{Note}	Ceramic resonator/ crystal resonator	$2.7~V \leq V_{\text{DD}} \leq 5.5~V$	1.0		20.0	MHz
		$2.4~V \leq V_{DD} < 2.7~V$	1.0		16.0	MHz
		$1.8~V \leq V_{DD} < 2.4~V$	1.0		8.0	MHz
		$1.6~V \leq V_{DD} < 1.8~V$	1.0		4.0	MHz
XT1 clock oscillation frequency (fx) ^{Note}	Crystal resonator		32	32.768	35	kHz

Note Indicates only permissible oscillator frequency ranges. Refer to AC Characteristics for instruction execution time. Request evaluation by the manufacturer of the oscillator circuit mounted on a board to check the oscillator characteristics.

Caution Since the CPU is started by the high-speed on-chip oscillator clock after a reset release, check the X1 clock oscillation stabilization time using the oscillation stabilization time counter status register (OSTC) by the user. Determine the oscillation stabilization time of the OSTC register and the oscillation stabilization time select register (OSTS) after sufficiently evaluating the oscillation stabilization time with the resonator to be used.

Remark When using the X1 oscillator and XT1 oscillator, refer to 5.4 System Clock Oscillator.

2.2.2 On-chip oscillator characteristics

 $(T_A = -40 \text{ to } +85^{\circ}\text{C}, 1.6 \text{ V} \le V_{DD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$

Oscillators	Parameters		Conditions	MIN.	TYP.	MAX.	Unit
High-speed on-chip oscillator clock frequency Notes 1, 2	fін			1		32	MHz
High-speed on-chip oscillator clock frequency accuracy		–20 to +85 °C	$1.8~V \leq V_{DD} \leq 5.5~V$	-1.0		+1.0	%
			$1.6~V \leq V_{DD} < 1.8~V$	-5.0		+5.0	%
		–40 to −20 °C	$1.8~V \leq V_{DD} \leq 5.5~V$	-1.5		+1.5	%
			$1.6~V \le V_{DD} < 1.8~V$	-5.5		+5.5	%
Low-speed on-chip oscillator clock frequency	fıL				15		kHz
Low-speed on-chip oscillator clock frequency accuracy				-15		+15	%

Notes 1. High-speed on-chip oscillator frequency is selected by bits 0 to 3 of option byte (000C2H/010C2H) and bits 0 to 2 of HOCODIV register.

2. This indicates the oscillator characteristics only. Refer to AC Characteristics for instruction execution time.

- Notes 1. Total current flowing into VDD, EVDDD, and EVDD1, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDDD, and EVDD1, or Vss, EVSSD, and EVSS1. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
 - 2. During HALT instruction execution by flash memory.
 - 3. When high-speed on-chip oscillator and subsystem clock are stopped.
 - **4.** When high-speed system clock and subsystem clock are stopped.
 - **5.** When high-speed on-chip oscillator and high-speed system clock are stopped. When RTCLPC = 1 and setting ultra-low current consumption (AMPHS1 = 1). The current flowing into the RTC is included. However, not including the current flowing into the 12-bit interval timer and watchdog timer.
 - 6. Not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
 - **7.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode: $2.7 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 32 \text{ MHz}$ $2.4 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 16 \text{ MHz}$ LS (low-speed main) mode: $1.8 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 8 \text{ MHz}$ LV (low-voltage main) mode: $1.6 \text{ V} \le \text{V}_{\text{DD}} \le 5.5 \text{ V} @ 1 \text{ MHz to } 4 \text{ MHz}$

- **8.** Regarding the value for current to operate the subsystem clock in STOP mode, refer to that in HALT mode.
- Remarks 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
 - 2. fin: High-speed on-chip oscillator clock frequency
 - 3. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - **4.** Except subsystem clock operation and STOP mode, temperature condition of the TYP. value is $T_A = 25^{\circ}C$

Remarks 1. p: CSI number (p = 00, 01, 10, 11, 20, 21, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3),

g: PIM and POM numbers (g = 0, 1, 4, 5, 8, 14)

2. fmck: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number,

n: Channel number (mn = 00 to 03, 10 to 13))

(4) During communication at same potential (CSI mode) (slave mode, SCKp... external clock input) (1/2)

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	Condit	ions	, ,	h-speed Mode	,	/-speed Mode	LV (low-voltage main) Mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCKp cycle time	tkcy2	$4.0~V \le EV_{DD0} \le 5.5$	20 MHz < fмск	8/fмск		_		_		ns
Note 5		V	fмск ≤ 20 MHz	6/ƒмск		6/fмск		6/fмск		ns
		$2.7~V \leq EV_{DD0} \leq 5.5$	16 MHz < fмск	8/fмск		_		_		ns
		V	fмск ≤ 16 MHz	6/ƒмск		6/fмск		6/fмск		ns
		2.4 V ≤ EV _{DD0} ≤ 5.5 V		6/fмск and 500		6/fмск and 500		6/fмск and 500		ns
		$1.8~V \leq EV_{DD0} \leq 5.5~V$		6/fмск and 750		6/fмск and 750		6/fмск and 750		ns
		$1.7~V \leq EV_{DDO} \leq 5.5~V$		6/fмск and 1500		6/fмск and 1500		6/fмск and 1500		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5	V	_		6/fмск and 1500		6/fмск and 1500		ns
SCKp high-/low- level width	tkH2, tkL2	4.0 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 7		tксү2/2 - 7		tkcy2/2 -7		ns
		$2.7~\text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5~\text{V}$		tксу2/2 — 8		tксу2/2 - 8		tkcy2/2 -8		ns
		1.8 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 – 18		tксу2/2 - 18		tксу2/2 - 18		ns
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		tксү2/2 — 66		tксү2/2 - 66		tkcy2/2 - 66		ns
		1.6 V ≤ EV _{DD0} ≤ 5.5 V				tксү2/2 - 66		tkcy2/2 - 66		ns

(Notes, Caution, and Remarks are listed on the next page.)

2.5.2 Serial interface IICA

(1) I2C standard mode

(Ta = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V)

Parameter	Symbol	С	Conditions	, ,	h-speed Mode	,	v-speed Mode	,	-voltage Mode	Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
SCLA0 clock frequency	fscL	Standard	$2.7 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V}$	0	100	0	100	0	100	kHz
		mode:	1.8 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
		fc∟k≥ 1 MHz	1.7 V ≤ EV _{DD0} ≤ 5.5 V	0	100	0	100	0	100	kHz
			1.6 V ≤ EV _{DD0} ≤ 5.5 V	_	_	0	100	0	100	kHz
Setup time of restart	tsu:sta	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
condition		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	4.7		4.7		μS
Hold time ^{Note 1}	thd:STA	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.8 V ≤ EV _{DD0} :	4.0		4.0		4.0		μS	
		1.7 V ≤ EV _{DD0} ≤ 5.5 V		4.0		4.0		4.0		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	4.0		4.0		μS
Hold time when SCLA0 =	tLOW	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
" <u>L</u> "		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	4.7		4.7		μS
Hold time when SCLA0 =	tніgн	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
"H"		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	4.0		4.0		μS
Data setup time	tsu:dat	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	250		250		250		ns
(reception)		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	250		250		250		ns
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	250		250		250		ns
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	-	_	250		250		ns
Data hold time	thd:dat	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
(transmission)Note 2		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	0	3.45	0	3.45	0	3.45	μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	0	3.45	0	3.45	μS
Setup time of stop	tsu:sto	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
condition		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.0		4.0		4.0		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	-	_	4.0		4.0		μS
Bus-free time	t BUF	2.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.8 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.7 V ≤ EV _{DD0} :	≤ 5.5 V	4.7		4.7		4.7		μS
		1.6 V ≤ EV _{DD0} ≤	≤ 5.5 V	_	_	4.7		4.7		μS

(Notes, Caution and Remark are listed on the next page.)



(2) When reference voltage (+) = AVREFP/ANIO (ADREFP1 = 0, ADREFP0 = 1), reference voltage (-) = AVREFM/ANI1 (ADREFM = 1), target pin : ANI16 to ANI26

(TA = -40 to +85°C, 1.6 V \leq EVDD0 = EVDD1 \leq VDD \leq 5.5 V, 1.6 V \leq AVREFP \leq VDD \leq 5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = AVREFP, Reference voltage (-) = AVREFM = 0 V)

Parameter	Symbol	Condit	ions	MIN.	TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error ^{Note 1}	AINL	10-bit resolution	$1.8~V \leq AV_{REFP} \leq 5.5~V$		1.2	±5.0	LSB
		$EV_{DD0} = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$\begin{array}{ c c c c }\hline 1.6 \ V \leq AV_{REFP} \leq 5.5 \ V^{Note} \\ & & & & & & \\ \hline \end{array}$		1.2	±8.5	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μS
		Target ANI pin : ANI16 to ANI26	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μS
			$1.8~V \leq V_{DD} \leq 5.5~V$	17		39	μS
			$1.6~V \leq V_{DD} \leq 5.5~V$	57		95	μS
Zero-scale error ^{Notes 1, 2}	Ezs	10-bit resolution EVDD0 = AVREFP = VDD Notes 3, 4	$1.8~V \leq AV_{REFP} \leq 5.5~V$			±0.35	%FSR
			$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Full-scale error ^{Notes 1, 2}	E _{FS}	10-bit resolution EVDD0 = AVREFP = VDD Notes 3, 4	$1.8~V \le AV_{REFP} \le 5.5~V$			±0.35	%FSR
			$1.6~V \leq AV_{REFP} \leq 5.5~V^{Note}$			±0.60	%FSR
Integral linearity error ^{Note}	ILE	10-bit resolution	$1.8~V \le AV_{REFP} \le 5.5~V$			±3.5	LSB
1		EVDD0 = AVREFP = VDD Notes 3, 4	$1.6~V \le AV_{REFP} \le 5.5~V^{Note}$			±6.0	LSB
Differential linearity	DLE	10-bit resolution	1.8 V ≤ AV _{REFP} ≤ 5.5 V			±2.0	LSB
error $^{Note 1}$ $EVDD0 = AV_{REFP} = V_{DD}^{Notes 3, 4}$	$1.6~V \le AV_{REFP} \le 5.5~V^{Note}$			±2.5	LSB		
Analog input voltage	VAIN	ANI16 to ANI26	,	0		AVREFP and EVDD0	٧

- **Notes 1.** Excludes quantization error (±1/2 LSB).
 - 2. This value is indicated as a ratio (%FSR) to the full-scale value.
 - 3. When $AV_{REFP} < V_{DD}$, the MAX. values are as follows.

Overall error: Add ± 1.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.05\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±0.5 LSB to the MAX. value when AVREFP = VDD.

- **4.** When $AV_{REFP} < EV_{DD0} \le V_{DD}$, the MAX. values are as follows.
 - Overall error: Add ± 4.0 LSB to the MAX. value when AV_{REFP} = V_{DD}.

Zero-scale error/Full-scale error: Add $\pm 0.20\%$ FSR to the MAX. value when AV_{REFP} = V_{DD}.

Integral linearity error/ Differential linearity error: Add ±2.0 LSB to the MAX. value when AVREFP = VDD.

5. When the conversion time is set to 57 μs (min.) and 95 μs (max.).

3. ELECTRICAL SPECIFICATIONS (G: INDUSTRIAL APPLICATIONS $T_A = -40$ to +105°C)

This chapter describes the following electrical specifications.

Target products G: Industrial applications $T_A = -40$ to +105°C R5F100xxGxx

- Cautions 1. The RL78 microcontrollers have an on-chip debug function, which is provided for development and evaluation. Do not use the on-chip debug function in products designated for mass production, because the guaranteed number of rewritable times of the flash memory may be exceeded when this function is used, and product reliability therefore cannot be guaranteed. Renesas Electronics is not liable for problems occurring when the on-chip debug function is used.
 - 2. With products not provided with an EVDD0, EVDD1, EVSS0, or EVSS1 pin, replace EVDD0 and EVDD1 with VDD, or replace EVSS0 and EVSS1 with VSS.
 - 3. The pins mounted depend on the product. Refer to 2.1 Port Function to 2.2.1 Functions for each product.
 - 4. Please contact Renesas Electronics sales office for derating of operation under $T_A = +85^{\circ}C$ to $+105^{\circ}C$. Derating is the systematic reduction of load for the sake of improved reliability.

Remark When RL78/G13 is used in the range of $T_A = -40$ to +85°C, see CHAPTER 2 ELECTRICAL SPECIFICATIONS ($T_A = -40$ to +85°C).

There are following differences between the products "G: Industrial applications ($T_A = -40$ to $+105^{\circ}$ C)" and the products "A: Consumer applications, and D: Industrial applications".

Parameter	Aŗ	oplication
	A: Consumer applications, D: Industrial applications	G: Industrial applications
Operating ambient temperature	T _A = -40 to +85°C	T _A = -40 to +105°C
Operating mode Operating voltage range	HS (high-speed main) mode: $2.7 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 32 \text{ MHz}$ $2.4 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 16 \text{ MHz}$ $LS \text{ (low-speed main) mode:}$ $1.8 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 8 \text{ MHz}$ $LV \text{ (low-voltage main) mode:}$ $1.6 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5 \text{ V} \textcircled{0}1 \text{ MHz to } 4 \text{ MHz}$	HS (high-speed main) mode only: $2.7~V \le V_{DD} \le 5.5~V @ 1~MHz~to~32~MHz$ $2.4~V \le V_{DD} \le 5.5~V @ 1~MHz~to~16~MHz$
High-speed on-chip oscillator clock accuracy	1.8 V \leq V _{DD} \leq 5.5 V \pm 1.0%@ T _A = -20 to +85°C \pm 1.5%@ T _A = -40 to -20°C 1.6 V \leq V _{DD} $<$ 1.8 V \pm 5.0%@ T _A = -20 to +85°C \pm 5.5%@ T _A = -40 to -20°C	$2.4 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$ $\pm 2.0\%$ \bigcirc T _A = +85 to +105°C $\pm 1.0\%$ \bigcirc T _A = -20 to +85°C $\pm 1.5\%$ \bigcirc T _A = -40 to -20°C
Serial array unit	UART CSI: fclk/2 (supporting 16 Mbps), fclk/4 Simplified I ² C communication	UART CSI: fclk/4 Simplified I ² C communication
IICA	Normal mode Fast mode Fast mode plus	Normal mode Fast mode
Voltage detector	Rise detection voltage: 1.67 V to 4.06 V (14 levels) Fall detection voltage: 1.63 V to 3.98 V (14 levels)	Rise detection voltage: 2.61 V to 4.06 V (8 levels) Fall detection voltage: 2.55 V to 3.98 V (8 levels)

(Remark is listed on the next page.)



Remark The electrical characteristics of the products G: Industrial applications (T_A = -40 to +105°C) are different from those of the products "A: Consumer applications, and D: Industrial applications". For details, refer to **3.1** to **3.10**.

3.1 Absolute Maximum Ratings

Absolute Maximum Ratings ($T_A = 25$ °C) (1/2)

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	V _{DD}		-0.5 to +6.5	٧
	EV _{DD0} , EV _{DD1}	EVDD0 = EVDD1	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8 and -0.3 to V _{DD} +0.3 ^{Note 1}	V
Input voltage	Vıı	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV _{DD0} +0.3	V
		P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	and -0.3 to V _{DD} +0.3 ^{Note 2}	
	V _{I2}	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137, P150 to P156, EXCLK, EXCLKS, RESET	-0.3 to V _{DD} +0.3 ^{Note 2}	V
Output voltage	V _{O1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47,	-0.3 to EV _{DD0} +0.3	٧
		P50 to P57, P60 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P130, P140 to P147	and -0.3 to V _{DD} +0.3 ^{Note 2}	
	V ₀₂	P20 to P27, P150 to P156	-0.3 to V _{DD} +0.3 Note 2	٧
Analog input voltage	VAI1	ANI16 to ANI26	-0.3 to EV _{DD0} +0.3 and -0.3 to AV _{REF} (+) +0.3 $^{\text{Notes 2, 3}}$	V
	V _{Al2}	ANI0 to ANI14	-0.3 to V _{DD} +0.3 and -0.3 to AV _{REF} (+) +0.3 $^{\text{Notes 2, 3}}$	V

- **Notes 1.** Connect the REGC pin to Vss via a capacitor (0.47 to 1 μ F). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.
 - 2. Must be 6.5 V or lower.
 - 3. Do not exceed AVREF(+) + 0.3 V in case of A/D conversion target pin.

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.

- **Remarks 1.** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.
 - **2.** $AV_{REF}(+)$: + side reference voltage of the A/D converter.
 - 3. Vss : Reference voltage



 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V}) (3/5)$

Items	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V _{IH1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0.8EV _{DD0}		EV _{DD0}	V
	V _{IH2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	2.2		EV _{DD0}	٧
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EVDD0 < 4.0 V	2.0		EV _{DD0}	V
			TTL input buffer 2.4 V ≤ EVDD0 < 3.3 V	1.5		EV _{DD0}	V
	V _{IH3}	P20 to P27, P150 to P156		0.7V _{DD}		V _{DD}	V
	V _{IH4}	P60 to P63	0.7EV _{DD0}		6.0	V	
	V _{IH5}	P121 to P124, P137, EXCLK, EXCL	0.8V _{DD}		V _{DD}	V	
Input voltage, low	V _{IL1}	P00 to P07, P10 to P17, P30 to P37, P40 to P47, P50 to P57, P64 to P67, P70 to P77, P80 to P87, P90 to P97, P100 to P106, P110 to P117, P120, P125 to P127, P140 to P147	Normal input buffer	0		0.2EV _{DD0}	V
	V _{IL2}	P01, P03, P04, P10, P11, P13 to P17, P43, P44, P53 to P55,	TTL input buffer 4.0 V ≤ EV _{DD0} ≤ 5.5 V	0		0.8	٧
		P80, P81, P142, P143	TTL input buffer 3.3 V ≤ EV _{DD0} < 4.0 V	0		0.5	V
			TTL input buffer 2.4 V ≤ EV _{DD0} < 3.3 V	0		0.32	V
	V _{IL3}	P20 to P27, P150 to P156		0		0.3V _{DD}	V
	VIL4	P60 to P63		0		0.3EV _{DD0}	V
	V _{IL5}	P121 to P124, P137, EXCLK, EXCL	(S, RESET	0		0.2V _{DD}	V

Caution The maximum value of V_{IH} of pins P00, P02 to P04, P10 to P15, P17, P43 to P45, P50, P52 to P55, P71, P74, P80 to P82, P96, and P142 to P144 is EV_{DD0}, even in the N-ch open-drain mode.

Remark Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

3.3.2 Supply current characteristics

(1) Flash ROM: 16 to 64 KB of 20- to 64-pin products (Ta = -40 to +105°C, 2.4 V \leq EVDD0 \leq VDD \leq 5.5 V, Vss = EVss0 = 0 V) (1/2)

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply current Note 1	IDD1	Operating mode	HS (high- speed main) mode Note 5	fін = 32 MHz ^{Note 3}	Basic operatio n	V _{DD} = 5.0 V		2.1		mA
						V _{DD} = 3.0 V		2.1		mA
					Normal	V _{DD} = 5.0 V		4.6	7.5	mA
					operatio n	V _{DD} = 3.0 V		4.6	7.5	mA
				f _{IH} = 24 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		3.7	5.8	mA
					operatio n	V _{DD} = 3.0 V		3.7	5.8	mA
				fih = 16 MHz ^{Note 3}	Normal	V _{DD} = 5.0 V		2.7	4.2	mA
					operatio n	V _{DD} = 3.0 V		2.7	4.2	mA
			HS (high- speed main) mode Note 5	$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		3.0	4.9	mA
				$V_{DD} = 5.0 \text{ V}$	operatio n	Resonator connection		3.2	5.0	mA
				$f_{MX} = 20 \text{ MHz}^{\text{Note 2}},$	Normal operation	Square wave input		3.0	4.9	mA
				$V_{DD} = 3.0 \text{ V}$		Resonator connection		3.2	5.0	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal operation	Square wave input		1.9	2.9	mA
				$V_{DD} = 5.0 \text{ V}$		Resonator connection		1.9	2.9	mA
				$f_{MX} = 10 \text{ MHz}^{\text{Note 2}},$	Normal	Square wave input		1.9	2.9	mA
				$V_{DD} = 3.0 \text{ V}$	operatio n	Resonator connection		1.9	2.9	mA
			Subsystem clock operation	fsuB = 32.768 kHz	Normal operatio n	Square wave input		4.1	4.9	μΑ
				Note 4 $T_A = -40^{\circ}C$		Resonator connection		4.2	5.0	μΑ
				fsuB = 32.768 kHz	Normal operatio n	Square wave input		4.1	4.9	μΑ
				Note 4 $T_A = +25^{\circ}C$		Resonator connection		4.2	5.0	μΑ
				fsub = 32.768 kHz Note 4 TA = +50°C	Normal	Square wave input		4.2	5.5	μΑ
					operatio n	Resonator connection		4.3	5.6	μΑ
				fsuB = 32.768 kHz Normal operatio TA = +70°C	Square wave input		4.3	6.3	μΑ	
						Resonator connection		4.4	6.4	μΑ
				fsuB = 32.768 kHz	Normal operation	Square wave input		4.6	7.7	μA
				Note 4		_ ' _ '		4.7	7.8	μΑ
				T _A = +85°C f _{SUB} = 32.768 kHz	Normal	Square wave input		6.9	19.7	,,Λ
				ISUB = 32.700 KHZ Note 4	operation	Resonator		7.0	19.7	μA μA
				T _A = +105°C		connection				

(Notes and Remarks are listed on the next page.)

- **6.** Current flowing only to the A/D converter. The supply current of the RL78 microcontrollers is the sum of IDD1 or IDD2 and IADC when the A/D converter is in operation.
- 7. Current flowing only to the LVD circuit. The supply current of the RL78 microcontrollers is the sum of IDD1, IDD2 or IDD3 and ILVD when the LVD circuit is in operation.
- 8. Current flowing only during data flash rewrite.
- **9.** Current flowing only during self programming.
- 10. For shift time to the SNOOZE mode, see 18.3.3 SNOOZE mode in the RL78/G13 User's Manual.
- Remarks 1. fil: Low-speed on-chip oscillator clock frequency
 - 2. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
 - 3. fclk: CPU/peripheral hardware clock frequency
 - **4.** Temperature condition of the TYP. value is $T_A = 25^{\circ}C$



3.4 AC Characteristics

$(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Items	Symbol	Conditions			MIN.	TYP.	MAX.	Unit
Instruction cycle (minimum	Тсу	Main system clock (fmain) operation	HS (high-speed main) mode	$2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}$	0.03125		1	μS
instruction execution time)				$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
		Subsystem clock (fsuB) 2.4 V ≤ V operation		$2.4~V \le V_{DD} \le 5.5~V$	28.5	30.5	31.3	μS
		In the self programming mode	(2.7 V ≤ V _{DD} ≤ 5.5 V	0.03125		1	μS
				$2.4 \text{ V} \le \text{V}_{DD} < 2.7 \text{ V}$	0.0625		1	μS
External system clock frequency	fex	$2.7~V \leq V_{DD} \leq 5.5~V$			1.0		20.0	MHz
		$2.4~V \leq V_{DD} < 2.7~V$			1.0		16.0	MHz
	fexs				32		35	kHz
External system clock input high-	texh, texl	$2.7~V \leq V_{DD} \leq 5.5~V$			24			ns
level width, low-level width		$2.4~V \leq V_{DD} < 2.7~V$			30			ns
	texhs, texhs				13.7			μS
TI00 to TI07, TI10 to TI17 input high-level width, low-level width	tтін, tті∟			1/fмск+10			ns ^{Note}	
TO00 to TO07, TO10 to TO17	fто	HS (high-spe	eed 4.0 V	≤ EV _{DD0} ≤ 5.5 V			16	MHz
output frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$			4	MHz
PCLBUZ0, PCLBUZ1 output	fPCL	HS (high-spe	eed 4.0 V	\leq EV _{DD0} \leq 5.5 V			16	MHz
frequency		main) mode	2.7 V	≤ EV _{DD0} < 4.0 V			8	MHz
			2.4 V	≤ EV _{DD0} < 2.7 V			4	MHz
Interrupt input high-level width,	tinth, tintl	INTP0	2.4 V	$\leq V_{DD} \leq 5.5 \text{ V}$	1			μS
low-level width		INTP1 to INT	TP11 2.4 V	$2.4~V \leq EV_{DD0} \leq 5.5~V$				μS
Key interrupt input low-level width	rrupt input low-level width the KR0 to KR7 $2.4 \text{ V} \le \text{EV}_{\text{DD0}} \le 5.5 \text{ V}$		≤ EV _{DD0} ≤ 5.5 V	250			ns	
RESET low-level width	trsl				10			μS

Note The following conditions are required for low voltage interface when $E_{VDD0} < V_{DD}$ $2.4V \le EV_{DD0} < 2.7 \text{ V}$: MIN. 125 ns

Remark fmck: Timer array unit operation clock frequency

(Operation clock to be set by the CKSmn0, CKSmn1 bits of timer mode register mn (TMRmn).

m: Unit number (m = 0, 1), n: Channel number (n = 0 to 7))

(6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output) (1/3)

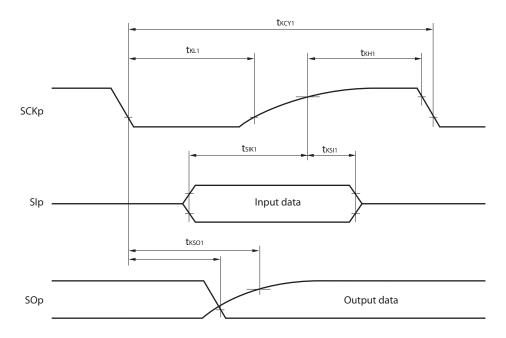
 $(T_A = -40 \text{ to } +105^{\circ}\text{C}, 2.4 \text{ V} \le \text{EV}_{DD0} = \text{EV}_{DD1} \le \text{V}_{DD} \le 5.5 \text{ V}, \text{Vss} = \text{EV}_{SS0} = \text{EV}_{SS1} = 0 \text{ V})$

Parameter	Symbol	Conditions		HS (high-speed main) Mode		Unit
				MIN.	MAX.	
SCKp cycle time	tkcy1	tkcy1 ≥ 4/fcLk	$4.0~V \leq EV_{DD0} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0$ $V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$	600		ns
			$2.7~V \leq EV_{DD0} < 4.0~V,~2.3~V \leq V_b \leq 2.7$ $V,$ $C_b = 30~pF,~R_b = 2.7~k\Omega$	1000		ns
			$2.4~V \leq EV_{DD0} < 3.3~V,~1.6~V \leq V_b \leq 2.0$ $V,$ $C_b = 30~pF,~R_b = 5.5~k\Omega$	2300		ns
SCKp high-level width	tкнı	4.0 V ≤ EV _{DD} C _b = 30 pF, F	$_{0}$ \leq 5.5 V, 2.7 V \leq V $_{b}$ \leq 4.0 V, R_{b} = 1.4 k Ω	tксу1/2 - 150		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF, F}$	$_{0}<4.0$ V, 2.3 V \leq V $_{b}\leq$ 2.7 V, $R_{b}=2.7$ k Ω	tkcy1/2 - 340		ns
		2.4 V ≤ EV _{DD} C _b = 30 pF, F	$_{0}$ < 3.3 V, 1.6 V \leq V $_{b}$ \leq 2.0 V, R_{b} = 5.5 k Ω	tксу1/2 - 916		ns
SCKp low-level width	t _{KL1}	$4.0~V \leq EV_{DD0} \leq 5.5~V,~2.7~V \leq V_b \leq 4.0~V,$ $C_b = 30~pF,~R_b = 1.4~k\Omega$		tkcy1/2 - 24		ns
		$2.7 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF, F}$	$0 < 4.0 \text{ V}, 2.3 \text{ V} \leq \text{V}_b \leq 2.7 \text{ V},$ $R_b = 2.7 \text{ k}\Omega$	tkcy1/2 - 36	36 ns	
		$2.4 \text{ V} \leq \text{EV}_{DD}$ $C_b = 30 \text{ pF}, \text{ F}$	$_{0}$ < 3.3 V, 1.6 V \leq V $_{b}$ \leq 2.0 V, R_{b} = 5.5 k Ω	tkcy1/2 - 100		ns

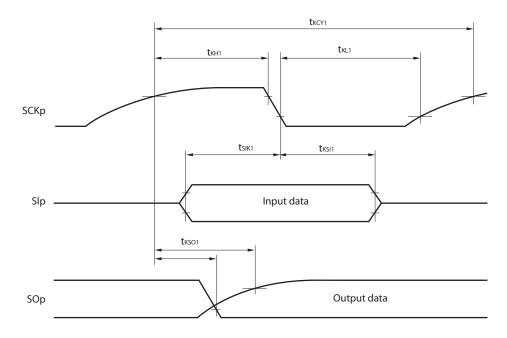
Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (Vpd tolerance (for the 20- to 52-pin products)/EVpd tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(Remarks are listed two pages after the next page.)

CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 1, or DAPmn = 1 and CKPmn = 0.)



Remarks 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 00, 01, 02, 10, 12, 13), n: Channel number (n = 0, 2), g: PIM and POM number (g = 0, 1, 4, 5, 8, 14)

2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.